

Docket No. 740756-2669

Serial No. 10/700,719

Page 13

REMARKS


In response to the Office Action dated February 27, 2006, Applicant hereby elects Group I (claims 1-5), drawn to an evaluation method by obtaining a threshold voltage and a flat band voltage from a drain current characteristics of a gate voltage of the semiconductor device; obtaining an activated dopant density from the threshold voltage and the flat band voltage.

Applicants have added new claim 30 to recite additional features of the present invention to which Applicants are entitled and amended claim 1 in order to correct minor typographical errors.

In addition to the above, applicants have amended the specification in order to also corrected minor typographical errors.

Consideration and allowance of the instant application are now respectfully requested.

Respectfully submitted,


Jeffrey L. Costellia
Registration No. 35,483

NIXON PEABODY LLP
Suite 900, 401 9th Street, N.W.
Washington, D.C. 20004-2128
(202) 585-8000